

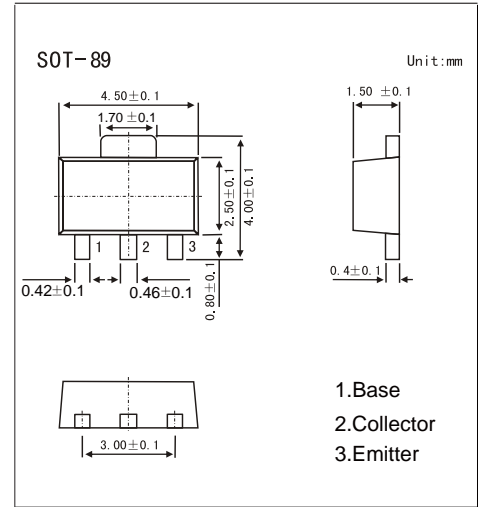
SOT-89 Plastic-Encapsulate Transistors

Features

- Low collector-to-emitter saturation voltage.
- Large current capacity and wide ASO.
- Fast switching speed.
- Complementary to 2SB1124
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-89 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

| Parameter | Symbol | Rating | Unit |
|-----------------------------------------|------------------|------------|------|
| Collector - Base Voltage | V _{CB0} | 60 | V |
| Collector - Emitter Voltage | V _{CEO} | 50 | |
| Emitter - Base Voltage | V _{EBO} | 6 | |
| Collector Current - Continuous | I _C | 3 | A |
| Collector Current - Pulse | I _{CP} | 6 | |
| Collector Power Dissipation (Note.1) | P _C | 0.5 | W |
| | | 1.5 | |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature Range | T _{stg} | -55 to 150 | |

Note.1:Mounted on ceramic board (250mm²×0.8mm)

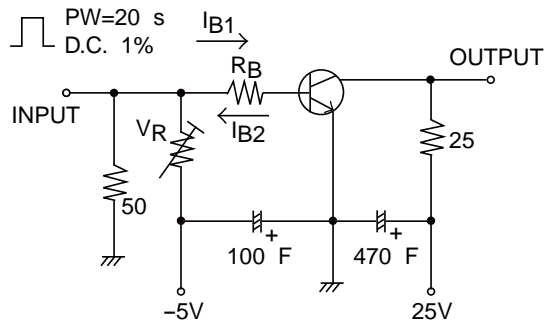
| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--------------------------------------|----------------------|---------------------------------------------------|-----|------|-----|------|
| Collector- base breakdown voltage | V _{CB0} | I _C = 100 uA, I _E = 0 | 60 | | | V |
| Collector- emitter breakdown voltage | V _{CEO} | I _C = 1 mA, R _{BE} = ∞ | 50 | | | |
| Emitter - base breakdown voltage | V _{EBO} | I _E = 100 uA, I _C = 0 | 6 | | | |
| Collector-base cut-off current | I _{CBO} | V _{CB} = 50 V, I _E = 0 | | | 1 | uA |
| Emitter cut-off current | I _{EBO} | V _{EB} = 4V, I _C =0 | | | 1 | |
| Collector-emitter saturation voltage | V _{CE(sat)} | I _C =2 A, I _B =100 mA | | 0.19 | 0.5 | V |
| Base - emitter saturation voltage | V _{BE(sat)} | I _C =2 A, I _B =100 mA | | | 1.2 | |
| DC current gain | h _{FE} | V _{CE} = 2V, I _C = 100 mA | 100 | | 560 | |
| | | V _{CE} = 2V, I _C = 3 A | 35 | | | |
| Turn-ON Time | t _{on} | See specified Test Circuit. | | 70 | | ns |
| Storage Time | t _{stg} | | | 650 | | |
| Fall Time | t _f | | | 35 | | |
| Collector output capacitance | C _{ob} | V _{CB} = 10V, I _E = 0, f=1MHz | | 25 | | pF |
| Transition frequency | f _r | V _{CE} = 10V, I _C = 50mA | | 150 | | MHz |

Classification of h_{FE}(1)

| Type | 2SD1624-R | 2SD1624-S | 2SD1624-T | 2SD1624-U |
|---------|-----------|-----------|-----------|-----------|
| Range | 100-200 | 140-280 | 200-400 | 280-560 |
| Marking | DG R* | DG S* | DG T* | DG U* |

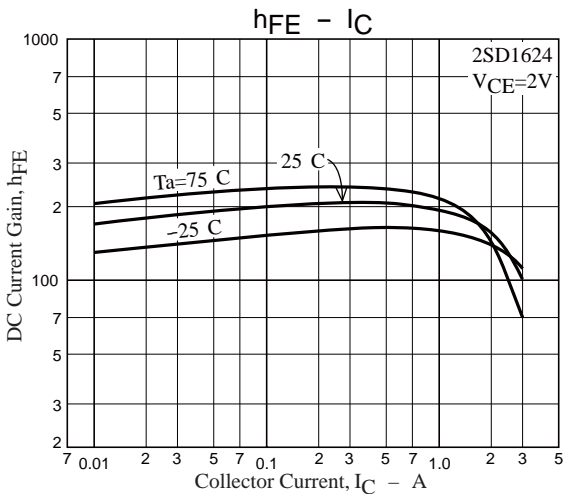
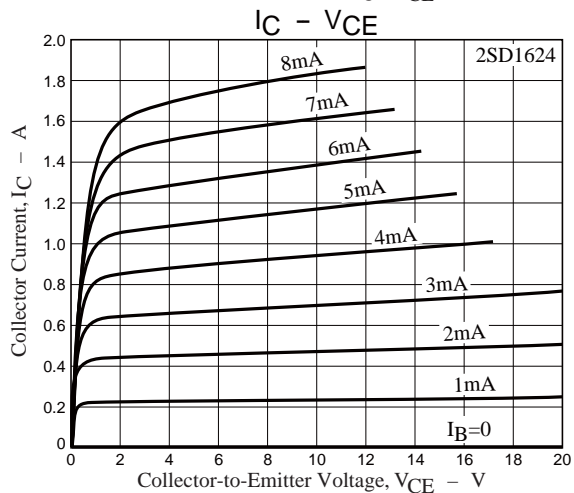
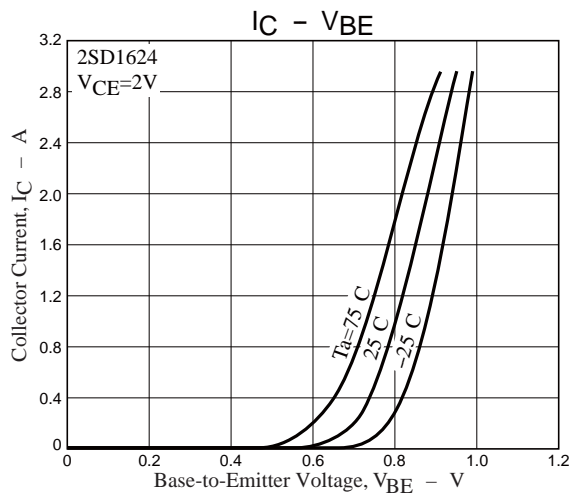
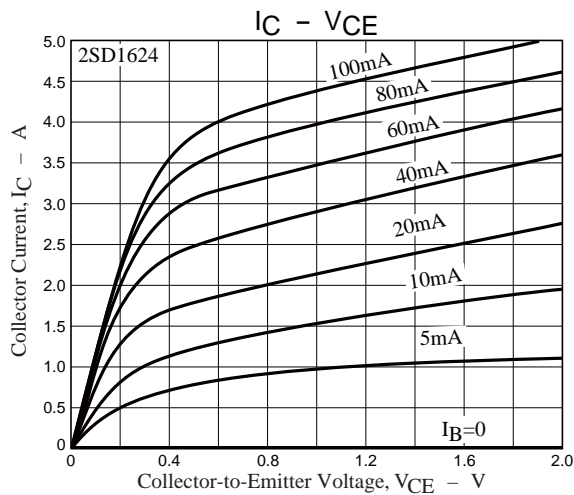
RATINGS AND CHARACTERISTIC CURVES

Switching Time Test Circuit



$10I_{B1} = -10I_{B2} = I_C = 1A$
(For PNP, the polarity is reversed.)

Typical Characteristics



RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

